ISO 17915:2018 (E)

Optics and photonics — Measurement method of semiconductor lasers for sensing

Contents

		Foreword	
		Introduction	
1		Scope	
2		Normative references	
3		Terms and definitions	
4		Optical sensing using semiconductor lasers	
	4.1	General	
	4.2	Semiconductor laser	
	4.2.		
	4.2.2		
	4.2.		
	4.2.4		
	4.2.		
	4.3	Common sensing technique and equipment using semiconductor lasers	
	4.3.		
	4.3.2		
	4.3.3		
	4.3.4	,	
	4.4	Temperature and current dependence of wavelength	
	4.5	Effect of current injection on lasing wavelength	
	4.6	Effect of ambient temperature on lasing wavelength	
5		Measurement method for temperature dependence of wavelength	
	5.1	General	
	5.2	Description of measurement setup and requirements	
	5.3	Precautions to be observed	
	5.4	Measurement procedures	
6		Measurement method for current dependence of wavelength	
	6.1	General	
	6.2	Description of measurement setup and requirements	
	6.3	Precautions to be observed	
	6.4	Measurement procedures	
	6.4.		
	6.4.2	2 Dynamic current coefficient	
7		Measurement method of spectral line width	
	7.1	General	
	7.2	Description of measurement setup and requirements	
	7.3	Precautions to be observed	
	7.4	Measurement procedures	
	7.4.2 7.4.2		
Annex	Α	(informative) Essential ratings and characteristics	
	A.1	General	
	A.2	Symbols (and abbreviated terms)	
	A.3	Essential ratings and characteristics of TO can laser devices	

A.3.1	Туре
A.3.2	Semiconductor material
A.3.3	Structure
A.3.4	Details of outline and encapsulation
A.3.5	Limiting values (absolute maximum system) over the operating temperature range, unless otherwise stated
A.3.6	Electrical and optical characteristics
A.3.7	Hazard
A.4	Essential ratings and characteristics of modules with pigtail fibre
A.4.1	Туре
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A.4.6	Electrical and optical characteristics
A.4.7	Hazard

Page count: 29